

20V Dual N-Channel Enhancement Mode MOSFET

Description

The NP9926A uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- ◆ $V_{DS} = 20V$, $I_D = 6.5A$
 $R_{DS(ON)}(\text{Typ.}) = 19m\Omega$ @ $V_{GS} = 2.5V$
 $R_{DS(ON)}(\text{Typ.}) = 14m\Omega$ @ $V_{GS} = 4.5V$
- ◆ High density cell design for ultra low R_{dson}
- ◆ Fully characterized avalanche voltage and current

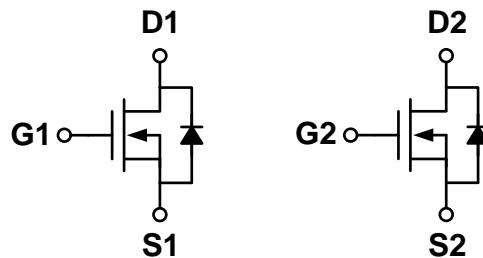
Application

- ◆ Power switching application
- ◆ Hard switched and high frequency circuits
- ◆ Uninterruptible power supply

Package

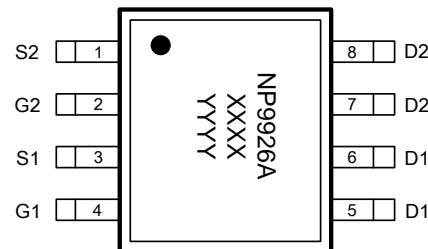
- ◆ SOP-8

Schematic diagram



Marking and pin assignment

**SOP-8
(TOP VIEW)**



Note: XXXX is the date code , YYYY is the wafer lot number.

Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
NP9926ASR	-55°C to +150°C	SOP-8	3000

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

parameter	symbol	limit	unit
Drain-source voltage	V_{DS}	20	V
Gate-source voltage	V_{GS}	± 12	V
Drain Current-Continuous (Silicon Limited)	I_D	6.5	A
		4	
Pulsed Drain Current (Package Limited)	I_{DM}	26	A
Maximum power dissipation	P_D	1.25	W
		0.8	
Operating junction Temperature range	T_j	-55—150	°C

Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF Characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	20	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =20V, V _{GS} =0V	-	-	1	μA
Gate-body leakage	I _{GSS}	V _{DS} =0V, V _{GS} =±12V	-	-	±100	nA
ON Characteristics						
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	-0.5	0.7	1.2	V
Drain-source on-state resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =6.5A	-	14	22	mΩ
		V _{GS} =2.5V, I _D =5.5A	-	19	27	
Forward transconductance	g _f	V _{GS} =5V, I _D =6A	-	10	-	S
Dynamic Characteristics						
Input capacitance	C _{ISS}	V _{DS} =10V, V _{GS} =0V f=1.0MHz	-	900	-	pF
Output capacitance	C _{OSS}		-	220	-	
Reverse transfer capacitance	C _{RSS}		-	100	-	
Switching Characteristics						
Turn-on delay time	t _{D(ON)}	V _{DD} =10V I _D =6A V _{GEN} =4.5V R _{GEN} =6ohm	-	10	-	ns
Rise time	tr		-	11	-	
Turn-off delay time	t _{D(OFF)}		-	35	-	
Fall time	tf		-	30	-	
Total gate charge	Q _g	V _{DS} =10V, I _D =6A V _{GS} =4.5V	-	12	-	nC
Gate-source charge	Q _{gs}		-	2.3	-	
Gate-drain charge	Q _{gd}		-	1	-	

Thermal Characteristics

Thermal Resistance junction-to ambient	R _{th JA}	100	°C/W
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Typical Performance Characteristics

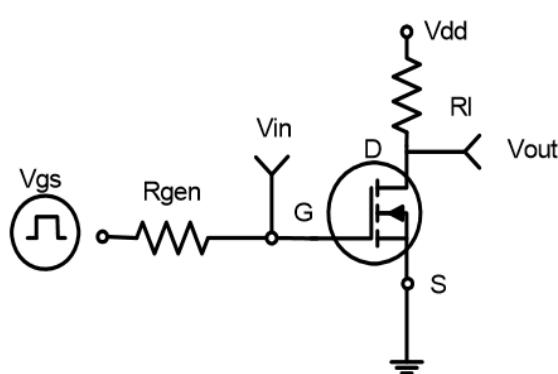


Figure 1:Switching Test Circuit

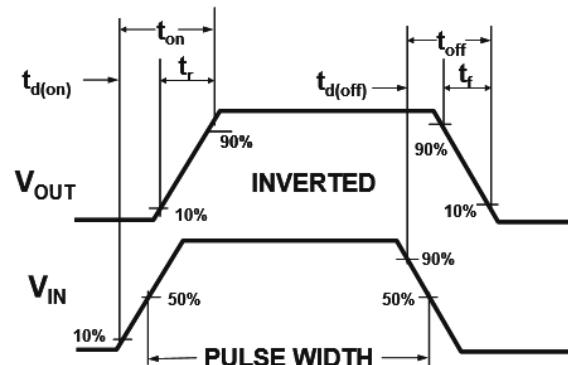


Figure 2:Switching Waveforms

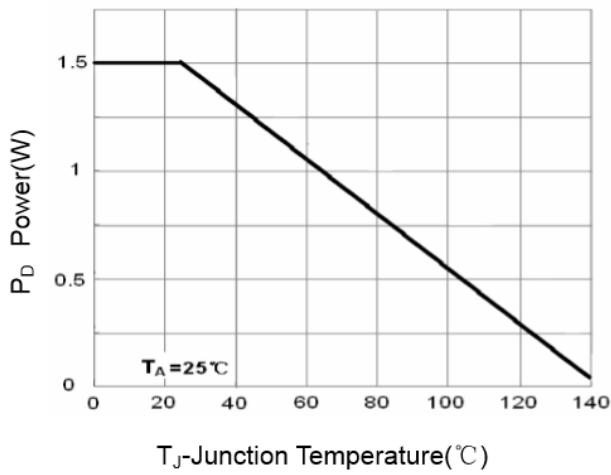


Figure 3 Power Dissipation
T_J-Junction Temperature(°C)

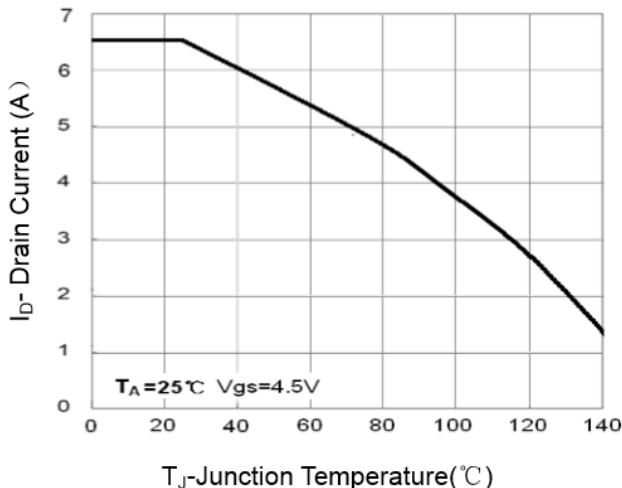


Figure 4 Drain Current
T_J-Junction Temperature(°C)

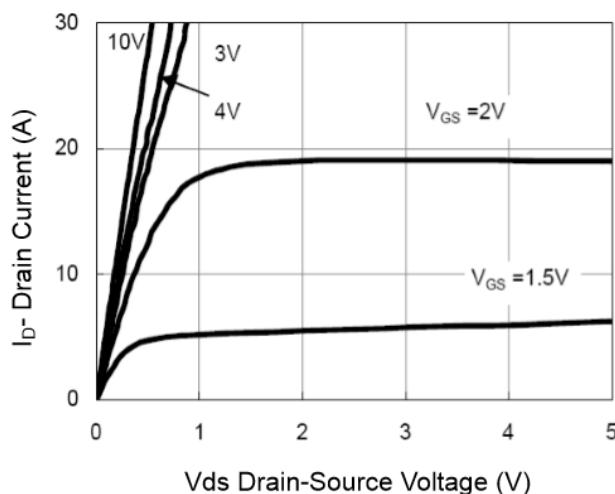


Figure 5 Output Characteristics

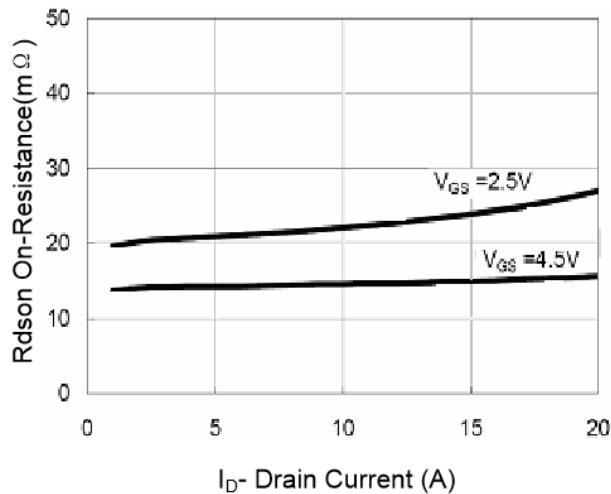
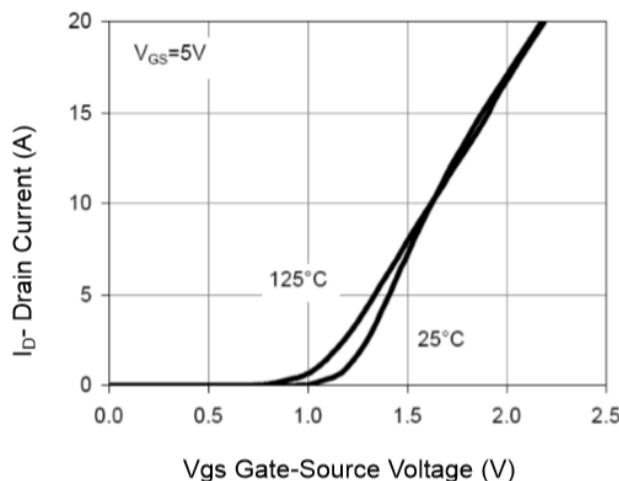
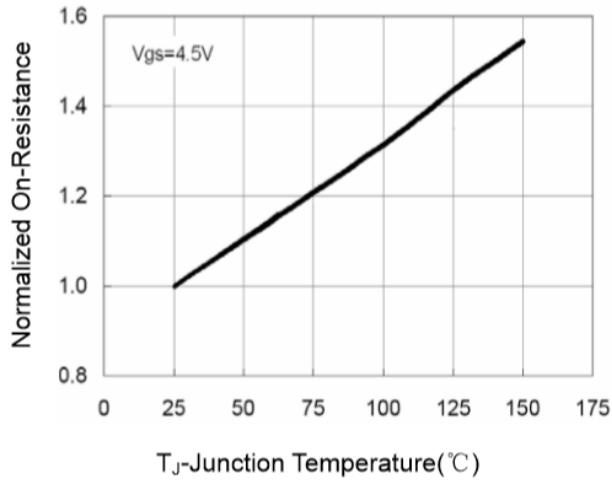
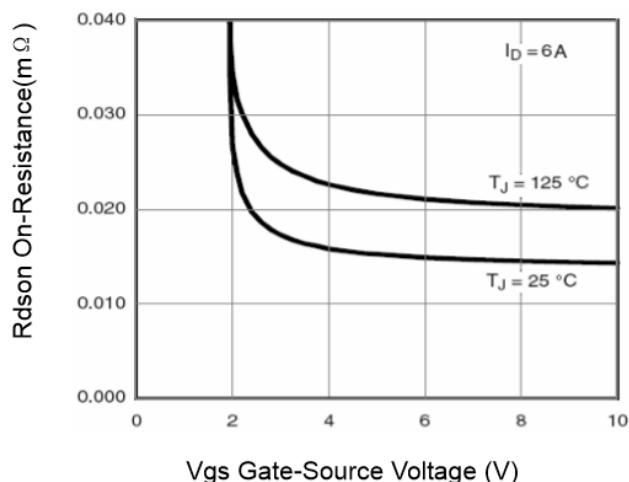
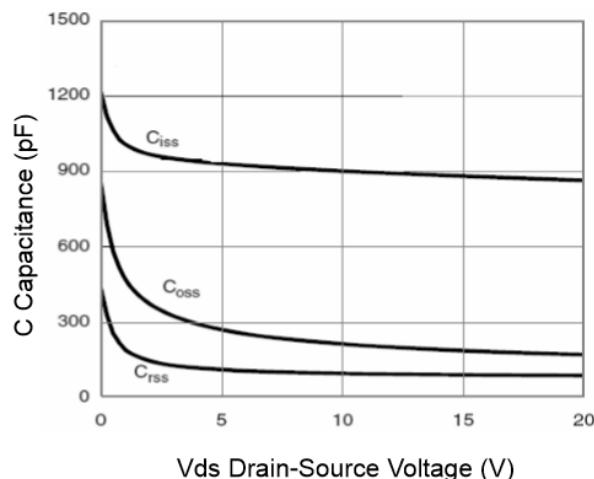
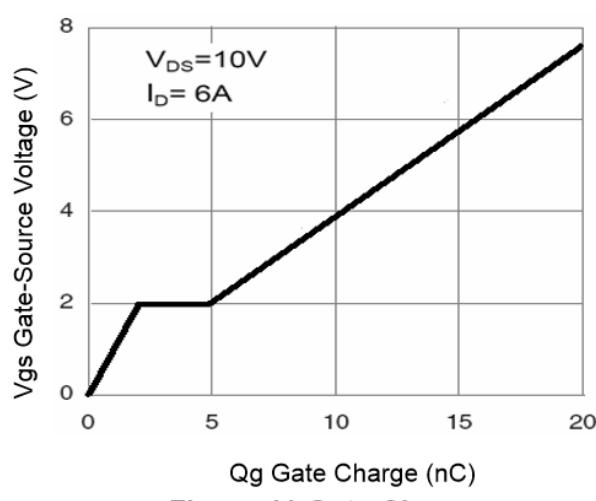
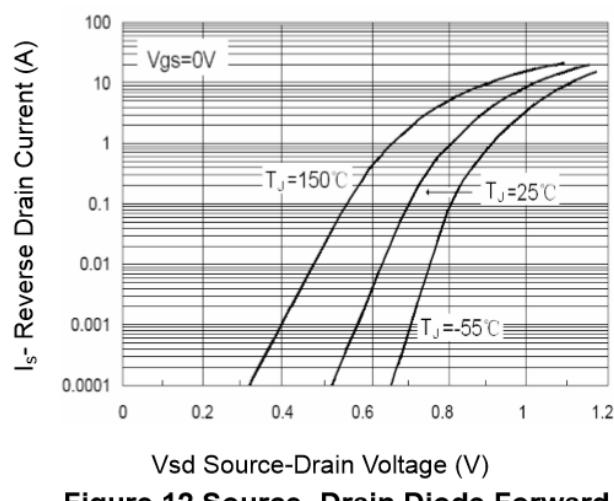


Figure 6 Drain-Source On-Resistance


Figure 7 Transfer Characteristics

Figure 8 Drain-Source On-Resistance

Figure 9 Rdson vs Vgs

Figure 10 Capacitance vs Vds

Figure 11 Gate Charge

Figure 12 Source-Drain Diode Forward

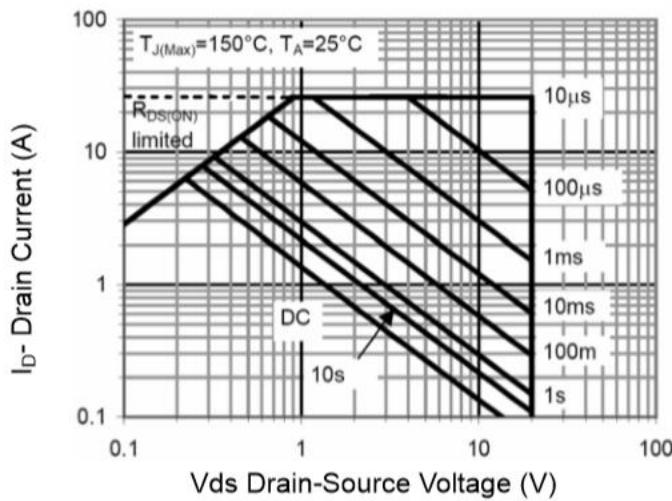


Figure 13 Safe Operation Area

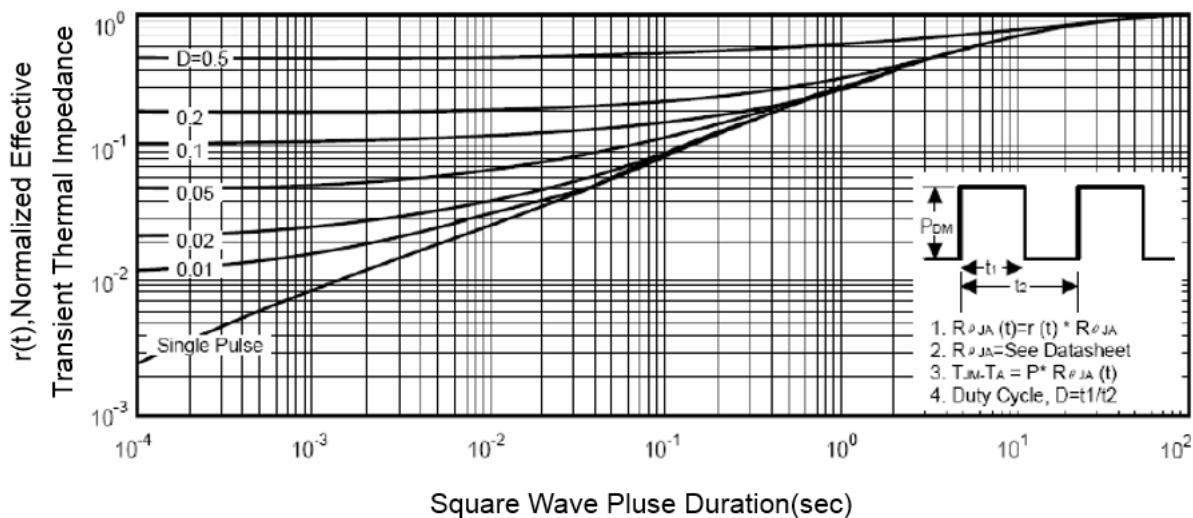
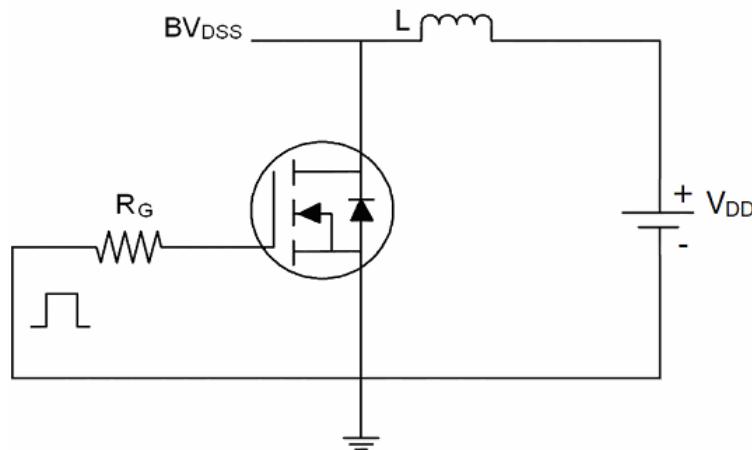


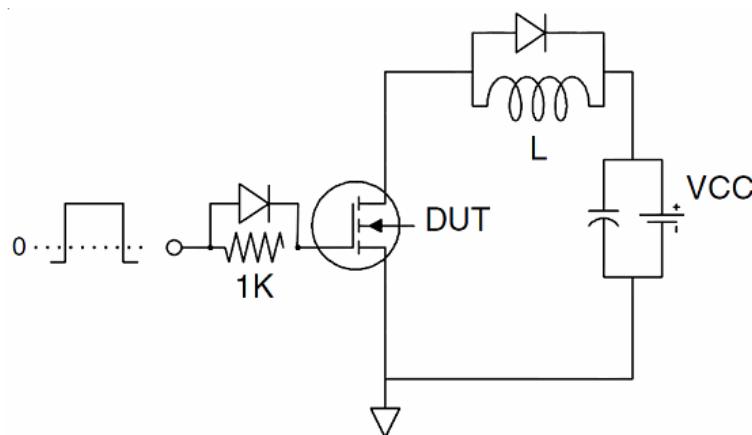
Figure 14 Normalized Maximum Transient Thermal Impedance

Test Circuit:

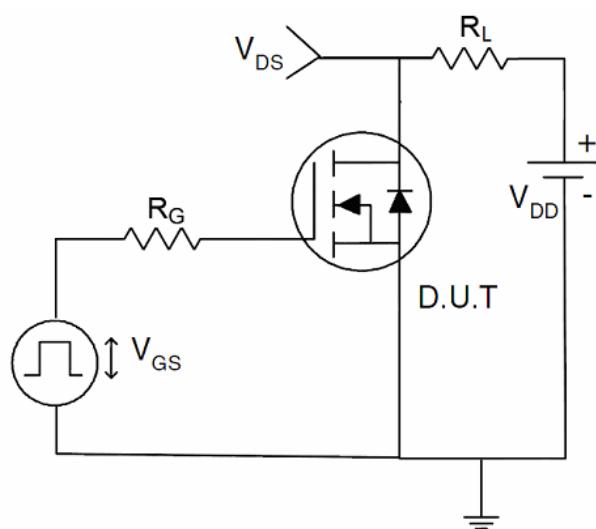
(1)、EAS Test Circuit



(2)、Gate Charge Test Circuit

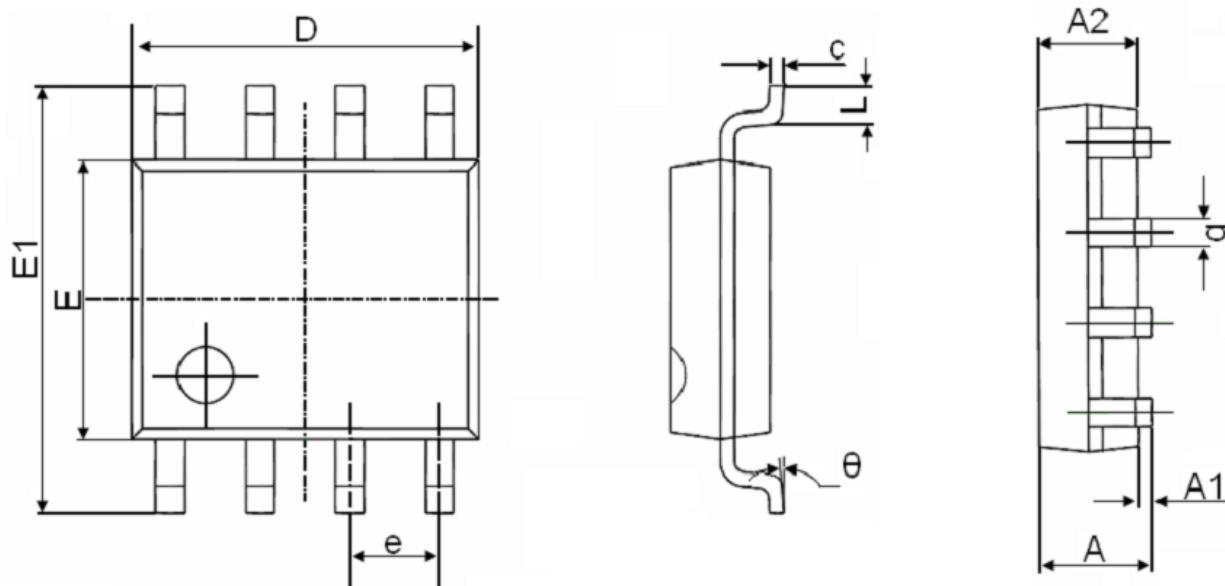


(3)、Switch Time Test Circuit



Package Information

- SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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[IPS60R360PFD7SAKMA1](#) [IPS60R600PFD7SAKMA1](#)